





SN65MLVD200A, SN65MLVD202A SN65MLVD204A, SN65MLVD205A

SLLS573-DECEMBER 2003

MULTIPOINT-LVDS LINE DRIVER AND RECEIVER

FEATURES

- Low-Voltage Differential 30- Ω to 55- Ω Line Drivers and Receivers for Signaling Rates (1) Up to 100 Mbps, Clock Frequencies up to 50 MHz
- Type-1 Receivers Incorporate 25 mV of Hysteresis (200A, 202A)
- Type-2 Receivers Provide an Offset(100 mV)
 Threshold to Detect Open-Circuit and Idle-Bus Conditions (204A, 205A)
- Meets or Exceeds the M-LVDS Standard TIA/EIA-899 for Multipoint Data Interchange
- Power Up/Down Glitch Free
- Controlled Driver Output Voltage Transition Times for Improved Signal Quality
- -1 V to 3.4 V Common-Mode Voltage Range Allows Data Transfer With 2 V of Ground Noise
- Bus Pins High Impedance When Disabled or $V_{CC} \le 1.5 \text{ V}$
- 200-Mbps Devices Available (SN65MLVD201, 203, 206, 207)
- Bus Pin ESD Protection Exceeds 8 kV
- Package in 8-Pin SOIC (200A, 204A) and 14-Pin SOIC (202A, 205A)
- Improved Alternatives to the SN65MLVD200, 202, 204, and 205

APPLICATIONS

- Low-Power High-Speed Short-Reach Alternative to TIA/EIA-485
- Backplane or Cabled Multipoint Data and Clock Transmission
- Cellular Base Stations
- Central-Office Switches
- Network Switches and Routers
- (1) The signaling rate of a line, is the number of voltage transitions that are made per second expressed in the nits bps (bits per second).

DESCRIPTION

The SN65MLVD200A, 202A, 204A, and 205A are multipoint-low-voltage differential (M-LVDS) line drivers and receivers, which are optimized to operate at signaling rates up to 100 Mbps. All parts comply with the multipoint low-voltage differential signaling (M-LVDS) standard TIA/EIA-899. These circuits are similar to their TIA/EIA-644 standard compliant LVDS counterparts, with added features to address multipoint applications. The driver output has been designed to support multipoint buses presenting loads as low as 30 Ω , and incorporates controlled transition times to allow for stubs off of the backbone transmission line.

These devices have Type-1 and Type-2 receivers that detect the bus state with as little as 50 mV of differential input voltage over a common-mode voltage range of -1 V to 3.4 V. The Type-1 receivers exhibit 25 mV of differential input voltage hysteresis to prevent output oscillations with slowly changing signals or loss of input. Type-2 receivers include an offset threshold to provide a known output state under open-circuit, idle-bus, and other fault conditions.

The SN65MLVD200A, 202A, 204A, and 205A have enhancements over their predecessors. Improved features include better controlled slew rate on the driver output to help minimize reflections while improving overall signal integrity (SI) resulting in better jitter performance. Additionally, 8-kV ESD protection on the bus pins for more robustness. The same footprint definition was maintained making for an easy drop-in replacement for a system performance upgrade.

The devices are characterized for operation from –40°C to 85°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

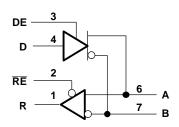




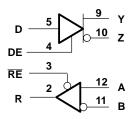
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

LOGIC DIAGRAM (POSITIVE LOGIC)

SN65MLVD200A, SN65MLVD204A



SN65MLVD202A, SN65MLVD205A



ORDERING INFORMATION

PART NUMBER (1)	FOOTPRINT	RECEIVER TYPE	PACKAGE MARKING
SN65MLVD200AD	SN75176	Type 1	MF200A
SM65MLVD202AD	SN75ALS180	Type 1	MLVD202A
SN65MLVD204AD	SN75176	Type 2	MF204A
SM65MLVD205AD	SN75ALS180	Type 2	MLVD205A

⁽¹⁾ Available tape and reeled. To order a tape and reeled part, add the suffix R to the part number (e.g., SN65MLVD200ADR).

PACKAGE DISSIPATION RATINGS

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 85°C POWER RATING
D(8)	532 mW	4.6 mW/°C	254 mW
D(14)	940 mW	8.2 mW/°C	450 mw

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted (1)

			SN65MLVD200A, 202A, 204A, and 205A	
Supply voltage range (2), V _{CC}			−0.5 V to 4 V	
	D, DE, RE		−0.5 V to 4 V	
Input voltage range	A, B (200A, 204A)		-1.8 V to 4 V	
	A, B (202A, 205A)	A, B (202A, 205A)		
Output voltage range	R		−0.3 V to 4 V	
Output voltage range	Y, Z, A, or B		-1.8 V to 4 V	
	Human Body Model (3)	A, B, Y, and Z	±8 kV	
Electrostatic discharge	numan body woder	All pins	±4 kV	
	Charged-Device Model ⁽⁴⁾	All pins	±1500 V	
Continuous power dissipat	tion		See Dissipation Rating Table	
Storage temperature range	е		−65°C to 150°C	

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

Tested in accordance with JEDEC Standard 22, Test Method A114-A. Tested in accordance with JEDEC Standard 22, Test Method C101.



RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	3	3.3	3.6	V
V_{IH}	High-level input voltage	2		V_{CC}	V
V_{IL}	Low-level input voltage	GND		8.0	V
	Voltage at any bus terminal V_A , V_B , V_Y or V_Z	-1.4		3.8	V
$ V_{ID} $	Magnitude of differential input voltage	0.05		V_{CC}	V
R_L	Differential load resistance	30	50		Ω
1/t _{UI}	Signaling rate			100	Mbps
T _A	Operating free-air temperature	-40		85	°C

DEVICE ELECTRICAL CHARACTERISTICS

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽⁽¹⁾	MAX	UNIT
		Driver only	$\overline{\text{RE}}$ and DE at V _{CC} , R _L = 50 Ω , All others open		13	22	
	Cupply ourrent	Both disabled	\overline{RE} at V_{CC} , DE at 0 V, R_L = No Load, All others open		1	4	mΛ
ICC	Supply current	Both enabled	$\overline{\text{RE}}$ at 0 V, DE at V _{CC} , R _L = 50 Ω , All others open		16	24	mA
		Receiver only	RE at 0 V, DE at 0 V, All others open		4	13	
P_D	Device power dis	sipation	R_L = 50 Ω, Input to D is a 50-MHz 50% duty cycle square wave, DE = high, \overline{RE} = low, T_A = 85°C			94	mW

⁽¹⁾ All typical values are at 25°C and with a 3.3-V supply voltage.

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DRIVER ELECTRICAL CHARACTERISTICS

	PARAMETER	TEST CONDITIONS	MIN ⁽¹⁾	TYP ⁽²⁾ MAX	UNIT
$ V_{AB} $ or $ V_{YZ} $	Differential output voltage magnitude	See Figure 2	480	650	mV
$\Delta V_{AB} $ or $\Delta V_{YZ} $	Change in differential output voltage magnitude between logic states	- See Figure 2	-50	50	mV
V _{OS(SS)}	Steady-state common-mode output voltage		0.8	1.2	V
$\Delta V_{OS(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 3	-50	50	mV
V _{OS(PP)}	Peak-to-peak common-mode output voltage			150	mV
$V_{Y(OC)}$ or $V_{A(OC)}$	Maximum steady-state open-circuit output voltage	See Figure 7	0	2.4	V
$V_{Z(OC)}$ or $V_{B(OC)}$	Maximum steady-state open-circuit output voltage	See Figure 7	0	2.4	V
$V_{P(H)}$	Voltage overshoot, low-to-high level output	See Figure 5		1.2 V _{SS}	V
$V_{P(L)}$	Voltage overshoot, high-to-low level output	See Figure 3	-0.2 V _{SS}		V
I_{IH}	High-level input current (D, DE)	$V_{IH} = 2 V \text{ to } V_{CC}$	0	10	μΑ
I _{IL}	Low-level input current (D, DE)	V_{IL} = GND to 0.8 V	0	10	μΑ
I _{os}	Differential short-circuit output current magnitude	See Figure 4		24	mA
I _{OZ}	High-impedance state output current (driver only)	$-1.4 \text{ V} \le (\text{V}_{\text{Y}} \text{ or } \text{V}_{\text{Z}}) \le 3.8 \text{ V},$ Other output = 1.2 V	-15	10	μA
I _{O(OFF)}	Power-off output current	$-1.4 \text{ V} \le (V_Y \text{ or } V_Z) \le 3.8 \text{ V}, \text{ Other output} = 1.2 \text{ V}, 0 \text{ V} \le V_{CC} \le 1.5 \text{ V}$	-10	10	μA
C _Y or C _Z	Output capacitance	V _I = 0.4 sin(30E6πt) + 0.5 V, ⁽³⁾ Other input at 1.2 V, driver disabled		3	pF
C _{YZ}	Differential output capacitance	$V_{AB} = 0.4 \sin(30E6\pi t) \text{ V, }^{(3)}$ Driver disabled		2.5	pF
C _{Y/Z}	Output capacitance balance, (C _Y /C _Z)		0.99	1.01	

The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet. All typical values are at 25°C and with a 3.3-V supply voltage.

HP4194A impedance analyzer (or equivalent)



RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V	Desitive seine differential input valtere threshold	Type 1				50	mV
V _{IT+}	Positive-going differential input voltage threshold	Type 2				150	mv
V	Negative gains differential input valtage throughold	Type 1	See Figure 9, Table 1 and Table	-50			mV
V _{IT-}	Negative-going differential input voltage threshold	Type 2	2	50			mv
V	Differential input voltage hyptogenia (// //)	Type 1			25		mV
V_{HYS}	Differential input voltage hysteresis, (V _{IT+} - V _{IT-})	Type 2			0		mv
V _{OH}	High-level output voltage		$I_{OH} = -8 \text{ mA}$	2.4			V
V _{OL}	Low-level output voltage		I _{OL} = 8 mA			0.4	V
I _{IH}	High-level input current (RE)		V _{IH} = 2 V to V _{CC}	-10		0	μΑ
I _{IL}	Low-level input current (RE)		V _{IL} = GND to 0.8 V	-10		0	μΑ
I _{OZ}	High-impedance output current		V _O = 0 V or 3.6 V	-10		15	μΑ
C _A or C _B			V _I = 0.4 sin(30E6πt) + 0.5 V, ⁽²⁾ Other input at 1.2 V		3		pF
C _{AB}	C _{AB} Differential input capacitance		$V_{AB} = 0.4 \sin(30E6\pi t) V^{(2)}$			2.5	pF
C _{A/B}	Input capacitance balance, (C _A /C _B)			0.99		1.01	

⁽¹⁾ All typical values are at 25°C and with a 3.3-V supply voltage.

BUS INPUT AND OUTPUT ELECTRICAL CHARACTERISTICS

	PARAMETER		TEST CONDITI	ONS	MIN	TYP ⁽¹⁾ MAX	UNIT
		V _A = 3.8 V,	V _B = 1.2 V,		0	32	
I_A	Receiver or transceiver with driver disabled input current	V _A = 0 V or 2.4 V, V _B = 1.2 V			-20	20	μA
	input duriont	V _A = -1.4 V,	V _B = 1.2 V		-32	0	
		V _B = 3.8 V,	V _A = 1.2 V		0	32	
I_{B}	Receiver or transceiver with driver disabled input current	$V_B = 0 \text{ V or } 2.4 \text{ V},$	V _A = 1.2 V		-20	20	μA
	pat cancer.	V _B = -1.4 V,	V _A = 1.2 V		-32	0	
I _{AB}	Receiver or transceiver with driver disabled differential input current (I _A – I _B)	$V_A = V_{B,}$	1.4 ≤ V _A ≤ 3.8	3 V	-4	4	μΑ
		V _A = 3.8 V,	V _B = 1.2 V,	0 V ≤ V _{CC} ≤ 1.5 V	0	32	
$I_{A(OFF)}$	Receiver or transceiver power-off input current	V _A = 0 V or 2.4 V,	V _B = 1.2 V,	0 V ≤ V _{CC} ≤ 1.5 V	-20	20	μA
		V _A = -1.4 V,	V _B = 1.2 V,	0 V ≤ V _{CC} ≤ 1.5 V	-32	0	
		V _B = 3.8 V,	V _A = 1.2 V,	0 V ≤ V _{CC} ≤ 1.5 V	0	32	
$I_{B(OFF)}$	Receiver or transceiver power-off input current	V _B = 0 V or 2.4 V,	V _A = 1.2 V,	0 V ≤ V _{CC} ≤ 1.5 V	-20	20	μA
		$V_B = -1.4 V$,	$V_A = 1.2 V$,	$0 \text{ V} \leq \text{V}_{\text{CC}} \leq 1.5 \text{ V}$	-32	0	
I _{AB(OFF)}	Receiver input or transceiver power-off differential input current $(I_A - I_B)$	$V_A = V_B$, $0 \text{ V} \le V_{CC} \le$	≤ 1.5 V, −1.4 ≤ V	V _A ≤ 3.8 V	-4	4	μΑ
C _A	Transceiver with driver disabled input capacitance	V _A = 0.4 sin (30E6π	t) + 0.5 V ⁽²⁾ , V _B	=1.2 V		5	pF
СВ	Transceiver with driver disabled input capacitance	$V_B = 0.4 \sin (30E6\pi t) + 0.5 V^{(2)}, V_A = 1.2 V$			5	pF	
C _{AB}	Transceiver with driver disabled differential input capacitance	V _{AB} = 0.4 sin (30E6πt)V ⁽²⁾			3	pF	
C _{A/B}	Transceiver with driver disabled input capacitance balance, (C _A /C _B)				0.99	1.01	

⁽¹⁾ All typical values are at 25°C and with a 3.3-V supply voltage.

⁽²⁾ HP4194A impedance analyzer (or equivalent)

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DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{pLH}	Propagation delay time, low-to-high-level output		2	2.5	3.5	ns
t _{pHL}	Propagation delay time, high-to-low-level output		2	2.5	3.5	ns
t _r	Differential output signal rise time	See Figure 5	2	2.6	3.2	ns
t _f	Differential output signal fall time	See Figure 5	2	2.6	3.2	ns
t _{sk(p)}	Pulse skew (t _{pHL} - t _{pLH})			30	150	ps
t _{sk(pp)}	Part-to-part skew				0.9	ns
t _{jit(per)}	Period jitter, rms (1 standard deviation) ⁽²⁾	50 MHz clock input ⁽³⁾		2	3	ps
t _{jit(pp)}	Peak-to-peak jitter ⁽²⁾⁽⁴⁾	100 Mbps 2 ¹⁵ -1 PRBS input ⁽⁵⁾		55	150	ps
t _{PHZ}	Disable time, high-level-to-high-impedance output			4	7	ns
t _{PLZ}	Disable time, low-level-to-high-impedance output	See Figure 6		4	7	ns
t _{PZH}	Enable time, high-impedance-to-high-level output	See Figure 0		4	7	ns
t _{PZL}	Enable time, high-impedance-to-low-level output			4	7	ns

- All typical values are at 25°C and with a 3.3-V supply voltage.
- Jitter is ensured by design and characterization. Stimulus jitter has been subtracted from the numbers.
- (3) $t_r = t_f = 0.5$ ns (10% to 90%), measured over 30 k samples.
- Peak-to-peak jitter includes jitter due to pulse skew $(t_{sk(p)})$.
- $t_r = t_f = 0.5 \text{ ns } (10\% \text{ to } 90\%), \text{ measured over } 100 \text{ k samples.}$

RECEIVER SWITCHING CHARACTERISTICS

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾ (1)	MAX	UNIT	
t _{PLH}	Propagation delay time, low-to-high-level output			2	3.6	6	ns	
t _{PHL}	Propagation delay time, high-to-low-level output			2	3.6	6	ns	
t _r	Output signal rise time			1		2.3	ns	
t _f	Output signal fall time		C _L = 15 pF, See Figure 10	1		2.3	ns	
	Dulge glyour (It to 1)	Type 1			100	300	ps	
t _{sk(p)}	Pulse skew ($ t_{pHL} - t_{pLH} $)		Type 2			300	500	ps
t _{sk(pp)}	Part-to-part skew ⁽²⁾					1	ns	
t _{jit(per)}	Period jitter, rms (1 standard deviation) ⁽³⁾		50 MHz clock input ⁽⁴⁾		4	7	ps	
	Pools to pools iittor(3)(5)	Type 1	100 Mbps 2 ¹⁵ –1 PRBS input ⁽⁶⁾		200	700	ps	
t _{jit(pp)}	Peak-to-peak jitter (4/14)	Peak-to-peak jitter ^{(3) (5)} Type 2 100 Mbps 2 ¹	100 Mbps 2:0-1 PRBS input(0)		225	800	ps	
t _{PHZ}	Disable time, high-level-to-high-impedance output				6	10	ns	
t _{PLZ}	Disable time, low-level-to-high-impedance output		See Figure 44		6	10	ns	
t _{PZH}	Enable time, high-impedance-to-high-level output		See Figure 11		10	15	ns	
t _{PZL}	Enable time, high-impedance-to-low-level output				10	15	ns	

- (1) All typical values are at 25°C and with a 3.3-V supply voltage.
- (2) HP4194A impedance analyzer (or equivalent)
- (3) Jitter is ensured by design and characterization. Stimulus jitter has been subtracted from the numbers.
- $V_{ID} = 200 \text{ mV}_{DD} \text{ (L/VD200A}, 202A), V_{ID} = 400 \text{ mV}_{DD} \text{ (LVD204A}, 205A), V_{cm} = 1 \text{ V, } t_r = t_f = 0.5 \text{ ns (10% to 90%), measured over 30 k}$
- (5) Peak-to-peak jitter includes jitter due to pulse skew $(t_{sk(p)})$. (6) $V_{ID} = 200 \text{ mV}_{pp}$ (LVD200A, 202A), $V_{ID} = 400 \text{ mV}_{pp}$ (LVD204A, 205A), $V_{cm} = 1 \text{ V}$, $t_r = t_f = 0.5 \text{ ns}$ (10% to 90%), measured over 100 k



PARAMETER MEASUREMENT INFORMATION

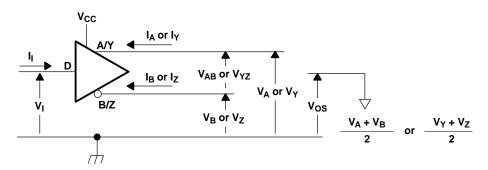
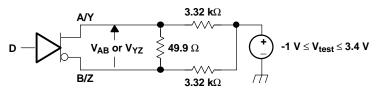
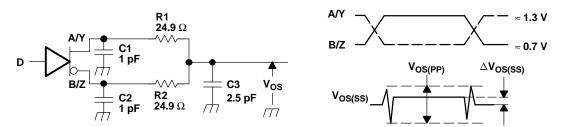


Figure 1. Driver Voltage and Current Definitions



A. All resistors are 1% tolerance.

Figure 2. Differential Output Voltage Test Circuit



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_r \le 1$ ns, pulse frequency = 1 MHz, duty cycle = $50 \pm 5\%$.
- B. C1, C2 and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are ±20%.
- C. R1 and R2 are metal film, surface mount, ±1%, and located within 2 cm of the D.U.T.
- D. The measurement of V_{OS(PP)} is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

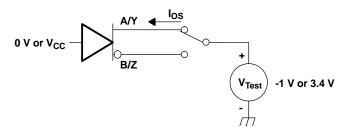
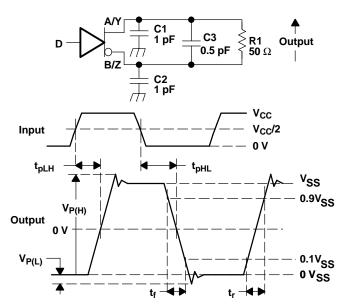


Figure 4. Driver Short-Circuit Test Circuit

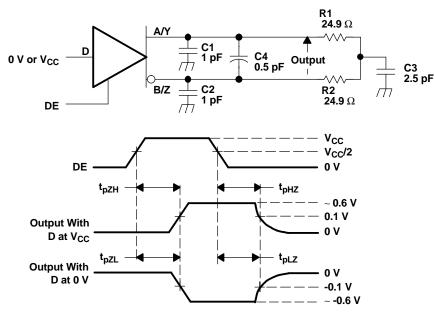


PARAMETER MEASUREMENT INFORMATION (continued)



- A. All input pulses are supplied by a generator having the following characteristics: t_r or t_f≤ 1 ns, frequency = 1 MHz, duty cycle = 50 ± 5%.
- B. C1, C2, and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are ±20%.
- C. R1 is a metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
- D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 5. Driver Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, frequency = 1 MHz, duty cycle = $50 \pm 5\%$.
- B. C1, C2, C3, and C4 includes instrumentation and fixture capacitance within 2 cm of the D.U.T. and are ±20%.
- C. R1 and R2 are metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
- D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 6. Driver Enable and Disable Time Circuit and Definitions



PARAMETER MEASUREMENT INFORMATION (continued)

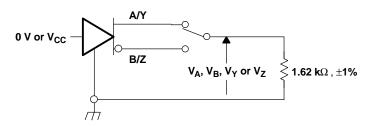
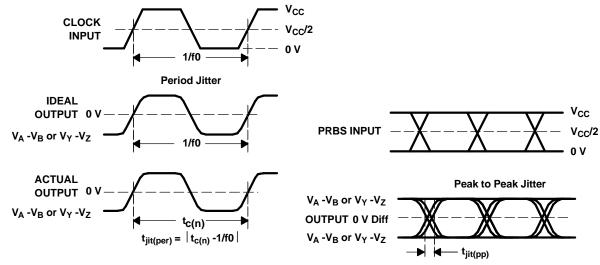


Figure 7. Maximum Steady State Output Voltage



- A. All input pulses are supplied by an Agilent 81250 Stimulus System.
- B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software
- C. Period jitter is measured using a 50 MHz 50 \pm 1% duty cycle clock input.
- D. Peak-to-peak jitter is measured using a 100Mbps 2¹⁵–1 PRBS input.

Figure 8. Driver Jitter Measurement Waveforms

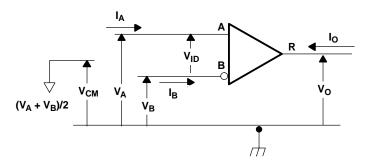


Figure 9. Receiver Voltage and Current Definitions



Table 1. Type-1 Receiver Input Threshold Test Voltages

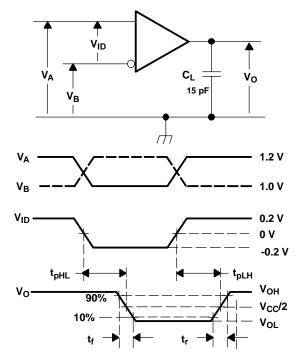
APPLIED \	OLTAGES	RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON- MODE INPUT VOLTAGE	RECEIVER
V _{IA}	V _{IB}	V_{ID}	V _{IC}	WOOTFOT
2.400	0.000	2.400	1.200	Н
0.000	2.400	-2.400	1.200	L
3.425	3.335	0.050	3.4	Н
3.375	3.425	-0.050	3.4	L
-0.975	-1.025	0.050	-1	Н
-1.025	-0.975	-0.050	-1	L

(1) H= high level, L = low level, output state assumes receiver is enabled $(\overline{RE} = L)$

Table 2. Type-2 Receiver Input Threshold Test Voltages

APPLIED V	OLTAGES	RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON- MODE INPUT VOLTAGE	RECEIVER OUTPUT ⁽¹⁾
V _{IA}	V _{IB}	V_{ID}	V _{IC}	OUTPUT
2.400	0.000	2.400	1.200	Н
0.000	2.400	-2.400	1.200	L
3.475	3.325	0.150	3.4	Н
3.425	3.375	0.050	3.4	L
-0.925	-1.075	0.150	–1	Н
-0.975	-1.025	0.050	–1	L

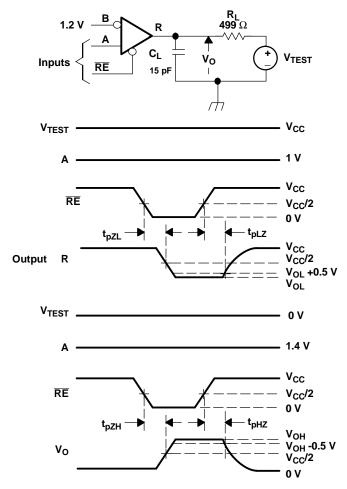
(1) H= high level, L = low level, output state assumes receiver is enabled $(\overline{RE} = L)$



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, frequency = 1 MHz, duty cycle = $50 \pm 5\%$. C_L is a combination of a 20%-tolerance, low-loss ceramic, surface-mount capacitor and fixture capacitance within 2 cm of the D.U.T.
- B. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 10. Receiver Timing Test Circuit and Waveforms

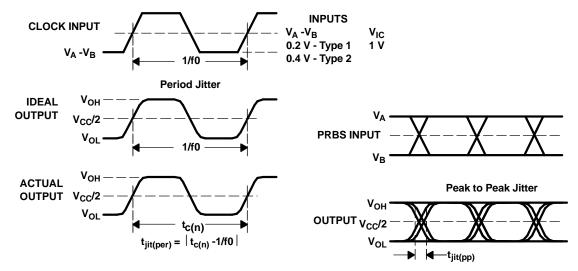




- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, frequency = 1 MHz, duty cycle = $50 \pm 5\%$.
- B. R_L is 1% tolerance, metal film, surface mount, and located within 2 cm of the D.U.T.
- C. C_L is the instrumentation and fixture capacitance within 2 cm of the DUT and $\pm 20\%$.

Figure 11. Receiver Enable/Disable Time Test Circuit and Waveforms

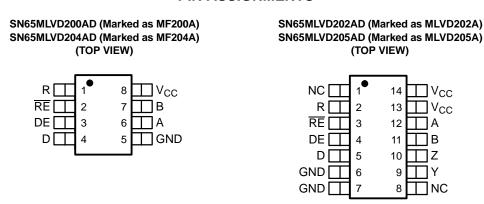




- A. All input pulses are supplied by an Agilent 8304A Stimulus System.
- B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software
- C. Period jitter is measured using a 50 MHz 50 ±1% duty cycle clock input.
- D. Peak-to-peak jitter is measured using a 100 Mbps 2¹⁵-1 PRBS input.

Figure 12. Receiver Jitter Measurement Waveforms

PIN ASSIGNMENTS



NC - No internal connection



DEVICE FUNCTION TABLES

TYPE-1 RECEIVER (200A, 202A)

111 2 11120211211 (20071) 20271)							
INPUTS	OUTPUT						
$V_{ID} = V_A - V_B$	RE	R					
V _{ID} ≥ 50 mV	L	Н					
$-50 \text{ mV} < V_{\text{ID}} < 50 \text{ mV}$	L	?					
$V_{ID} \le -50 \text{ mV}$	L	L					
X	Н	Z					
X	Open	Z					
Open Circuit	L	?					

TYPE-2 RECEIVER (204A, 205A)

INPUTS	OUTPUT	
$V_{ID} = V_A - V_B$	RE	R
V _{ID} ≥ 150 mV	L	Н
50 mV < V _{ID} < 150 mV	L	?
$V_{ID} \le 50 \text{ mV}$	L	L
X	Н	Z
X	Open	Z
Open Circuit	L	L

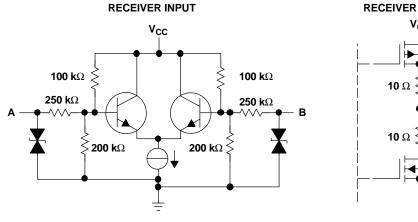
DRIVER

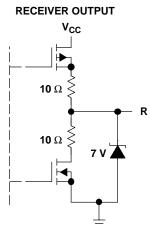
INPUT	ENABLE	OUTPUTS				
D	DE	A OR Y	B OR Z			
L	Н	L	Н			
Н	Н	Н	L			
OPEN	Н	L	Н			
Х	OPEN	Z	Z			
Х	L	Z	Z			

H = high level, L = low level, Z = high impedance, X = Don't care, ? = indeterminate

EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

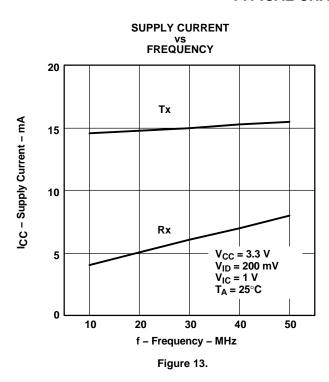
DRIVER INPUT AND DRIVER ENABLE V_{CC} $V_$



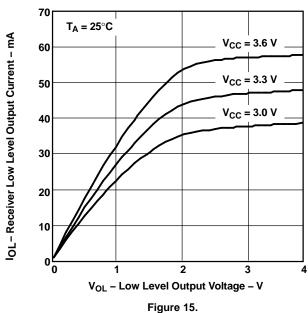




TYPICAL CHARACTERISTICS



RECEIVER LOW-LEVEL OUTPUT CURRENT vs LOW-LEVEL OUTPUT VOLTAGE



SUPPLY CURRENT vs FREE-AIR TEMPERATURE

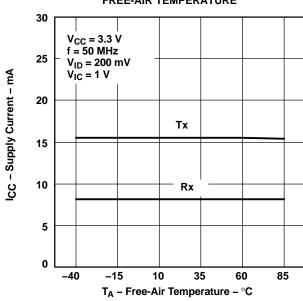


Figure 14.

RECEIVER HIGH-LEVEL OUTPUT CURRENT vs HIGH-LEVEL OUTPUT VOLTAGE

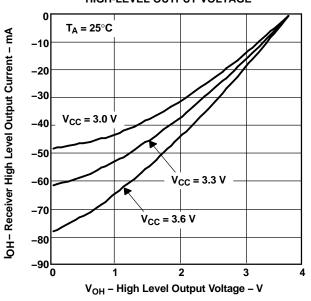
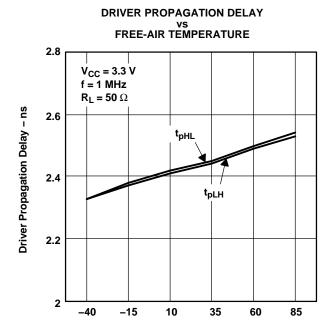


Figure 16.

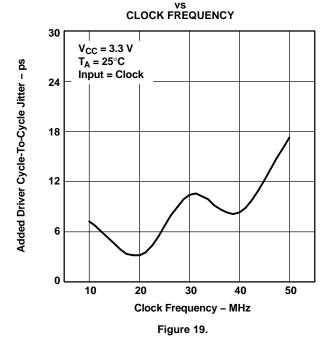


TYPICAL CHARACTERISTICS (continued)



ADDED DRIVER CYCLE-TO-CYCLE JITTER

T_A – Free-Air Temperature – °C Figure 17.



RECEIVER PROPAGATION DELAY vs FREE-AIR TEMPERATURE

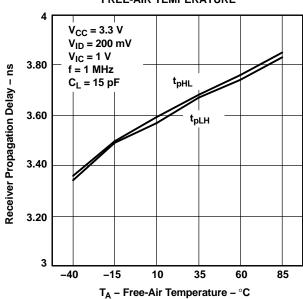


Figure 18.

ADDED DRIVER PEAK-TO-PEAK JITTER VS SIGNALING RATE

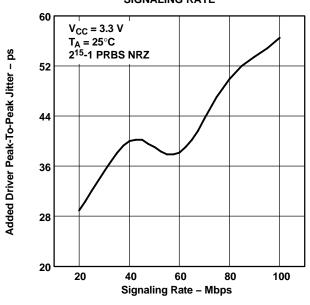
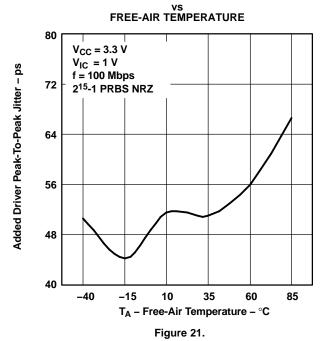


Figure 20.

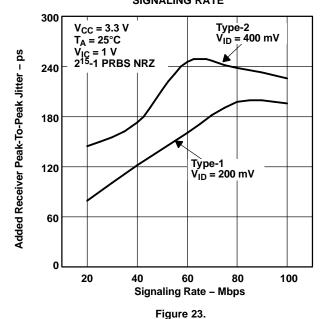


TYPICAL CHARACTERISTICS (continued)

ADDED DRIVER PEAK-TO-PEAK JITTER vs



ADDED RECEIVER PEAK-TO-PEAK JITTER vs SIGNALING RATE



ADDED RECEIVER CYCLE-TO-CYCLE JITTER vs CLOCK FREQUENCY

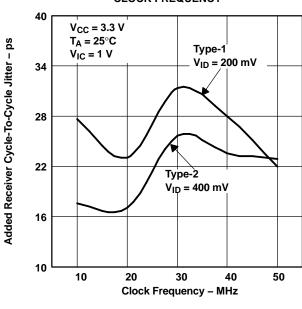
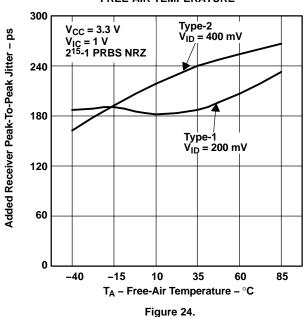


Figure 22.

ADDED RECEIVER PEAK-TO-PEAK JITTER vs FREE-AIR TEMPERATURE

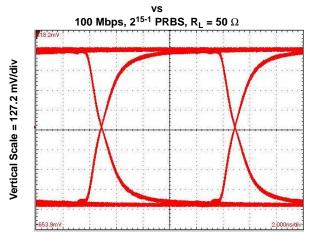


16



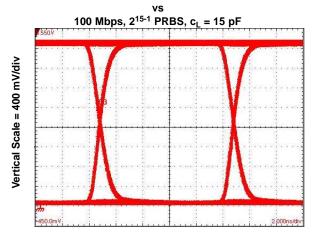
TYPICAL CHARACTERISTICS (continued)

SN65MLVD200A DRIVER OUTPUT EYE PATTERN



Horizontal Scale = 2 ns/div Figure 25.

SN65MLVD200A RECEIVER OUTPUT EYE PATTERN



Horizontal Scale = 2 ns/div Figure 26.



APPLICATION INFORMATION

COMPARISON OF MLVD TO TIA/EIA-485

Receiver Input Threshold (Failsafe)

The MLVD standard defines a type 1 and type 2 receiver. Type 1 receivers include no provisions for failsafe and have their differential input voltage thresholds near zero volts. Type 2 receivers have their differential input voltage thresholds offset from zero volts to detect the absence of a voltage difference. The impact to receiver output by the offset input can be seen in Table 3 and Figure 27.

Table 3. Receiver Input Voltage Threshold Requirements

RECEIVER TYPE	OUTPUT LOW	OUTPUT HIGH
Type 1	$-2.4 \text{ V} \le \text{V}_{\text{ID}} \le -0.05 \text{ V}$	$0.05 \text{ V} \le \text{V}_{\text{ID}} \le 2.4 \text{ V}$
Type 2	$-2.4 \text{ V} \le \text{V}_{\text{ID}} \le 0.05 \text{ V}$	$0.15 \text{ V} \le \text{V}_{\text{ID}} \le 2.4 \text{ V}$

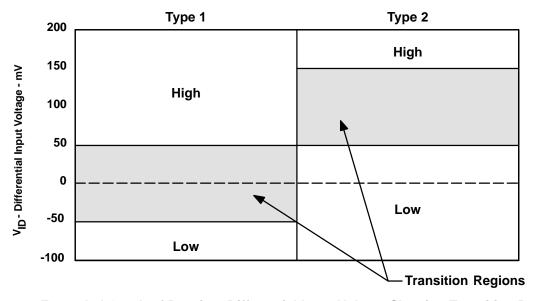


Figure 27. Expanded Graph of Receiver Differential Input Voltage Showing Transition Region





i.com 8-Jan-2007

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65MLVD200AD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD200ADG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD200ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD200ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD202AD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD202ADG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD202ADR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD202ADRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD204AD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD204ADG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD204ADR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD204ADRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD205AD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD205ADG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD205ADR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65MLVD205ADRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



PACKAGE OPTION ADDENDUM

8-Jan-2007

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

_		
I		Dimension designed to accommodate the component width
I	B0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
- [P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65MLVD200ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65MLVD202ADR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN65MLVD204ADR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65MLVD205ADR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1





*All dimensions are nominal

7 til dillionono di o momina							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65MLVD200ADR	SOIC	D	8	2500	340.5	338.1	20.6
SN65MLVD202ADR	SOIC	D	14	2500	333.2	345.9	28.6
SN65MLVD204ADR	SOIC	D	8	2500	340.5	338.1	20.6
SN65MLVD205ADR	SOIC	D	14	2500	333.2	345.9	28.6

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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